

Mahitosh Biswas

List of Publications by Year in descending order

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Version: 2024-02-01

14
papers

76
citations

1684188

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1474206

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#	ARTICLE	IF	CITATIONS
1	Thermodynamically metastable $\text{In}_{1-x}\text{Ga}_x\text{N}$, $\text{In}_{1-x}\text{Ga}_x\text{N}$ (or $\text{In}_{1-x}\text{Ga}_x\text{N}$), and $\text{In}_{1-x}\text{Ga}_x\text{N}$ -Ga ₂ O ₃ : From material growth to device applications. APL Materials, 2022, 10, .	5.1	23
2	Growth of high quality (In,Ga)N films on O-face ZnO substrates by plasma-assisted molecular beam epitaxy. AIP Advances, 2020, 10, .	1.3	4
3	Effects of rapid thermal annealing in InGaN/GaN quantum disk-in-GaN nanowire arrays. Journal of Luminescence, 2020, 222, 117123.	3.1	2
4	Engineering of carrier localization in BGaAs SQW for novel intermediate band solar cells: Thermal annealing effect. Solar Energy, 2020, 199, 183-191.	6.1	12
5	Enhanced optical and structural properties of MBE-grown AlGaIn nanowires on Si substrate by H-ion implantation and UV ozone treatment. , 2019, , .		1
6	Passivation of Surface States of AlGaIn Nanowires Using H ₂ PO ₄ Treatment To Enhance the Performance of UV-LEDs and Photoanodes. ACS Applied Nano Materials, 2018, 1, 1968-1975.	5.0	9
7	Vertical strain-induced dot size uniformity and thermal stability of InAs/GaN/GaAs coupled quantum dots. Journal of Alloys and Compounds, 2018, 748, 601-607.	5.5	4
8	Ultrathin GaAsN matrix-induced reduced full width at half maximum of GaAsN/InAs/GaAsN dot-in-a-well heterostructures with extended emission wavelength. Journal of Luminescence, 2018, 194, 341-345.	3.1	5
9	High nitrogen composition-induced low interfacial roughness of GaAs _{0.978} N _{0.022} /GaAs multiple quantum wells grown through solid-source molecular beam epitaxy. Materials Research Bulletin, 2017, 88, 242-247.	5.2	3
10	Varying nitrogen background pressure; an efficient approach to improve electrical properties of MBE-grown GaAs _{1-x} N _x thin films with less atomic disorder. Journal of Alloys and Compounds, 2017, 695, 3163-3169.	5.5	7
11	Annihilation of arsenic-nitrogen bonding defects in annealed InAs _{1-x} N _x quantum dots grown through nitrogen background pressure-controlled SS-MBE. Journal of Alloys and Compounds, 2017, 722, 287-292.	5.5	1
12	A low temperature investigation of the optical properties of coupled InAs quantum dots with GaAsN/GaAs spacers. Proceedings of SPIE, 2017, , .	0.8	1
13	Defect annihilation-mediated enhanced activation energy of GaAs _{0.979} N _{0.021} -capped InAs/GaAs quantum dots by H ⁺ ion implantation. Thin Solid Films, 2017, 639, 73-77.	1.8	4
14	CAD Model to Predict the Effect of Radome on the Characteristics of Rectangular Patch Antenna. Microwave and Optical Technology Letters, 2013, 55, 2460-2468.	1.4	0